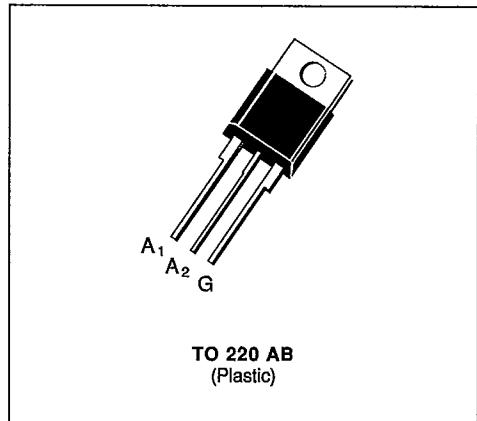


**S G S-THOMSON****SENSITIVE GATE TRIACS**

- GLASS PASSIVATED CHIP
- I<sub>G</sub>T SPECIFIED IN FOUR QUADRANTS
- AVAILABLE IN INSULATED VERSION →  
BTA SERIES (INSULATING VOLTAGE  
2500 V<sub>RMS</sub>) OR IN UNINSULATED VERSION  
→ BTB SERIES
- UL RECOGNIZED FOR BTA SERIES (E81734)

**DESCRIPTION**

New range suited for applications such as phase control and static switching.

**ABSOLUTE RATINGS (limiting values)**

Symbol	Parameter	Value	Unit
I <sub>T(RMS)</sub>	RMS on-state Current (360° conduction angle)	8	A
I <sub>TSM</sub>	Non Repetitive Surge Peak on-state Current (T <sub>j</sub> initial = 25 °C - Half sine wave)	t = 8.3 ms	A
		t = 10 ms	
I <sup>2</sup> t	I <sup>2</sup> t Value for Fusing	32	A <sup>2</sup> s
dI/dt	Critical Rate of Rise of on-state Current (1)	Repetitive F = 50 Hz	A/μs
		Non Repetitive	
T <sub>stg</sub> T <sub>j</sub>	Storage and Operating Junction Temperature Range	- 40 to 150 - 40 to 110	°C °C

Symbol	Parameter	BTA/BTB 08-					Unit
		200S	400S	600S	700S	800S	
V <sub>DRM</sub>	Repetitive Peak off-state Voltage (2)	200	400	600	700	800	V

(1) I<sub>g</sub> = 100 mA dI/dt = 1 A/μs(2) T<sub>j</sub> = 110 °C.**THERMAL RESISTANCES**

Symbol	Parameter	Value	Unit
R <sub>th (J-a)</sub>	Junction to Ambient	60	°C/W
R <sub>th (J-c) DC</sub>	Junction to Case for DC	5.1	°C/W
R <sub>th (J-c) AC</sub>	Junction to Case for 360 ° Conduction Angle (F = 50 Hz)	3.8	°C/W

## GATE CHARACTERISTICS (maximum values)

$P_{GM} = 40 \text{ W}$  ( $t_p = 10 \mu\text{s}$ )       $I_{GM} = 4 \text{ A}$  ( $t_p = 10 \mu\text{s}$ )  
 $P_{G(AV)} = 1 \text{ W}$        $V_{GM} = 16 \text{ V}$  ( $t_p = 10 \mu\text{s}$ )

T-25-15

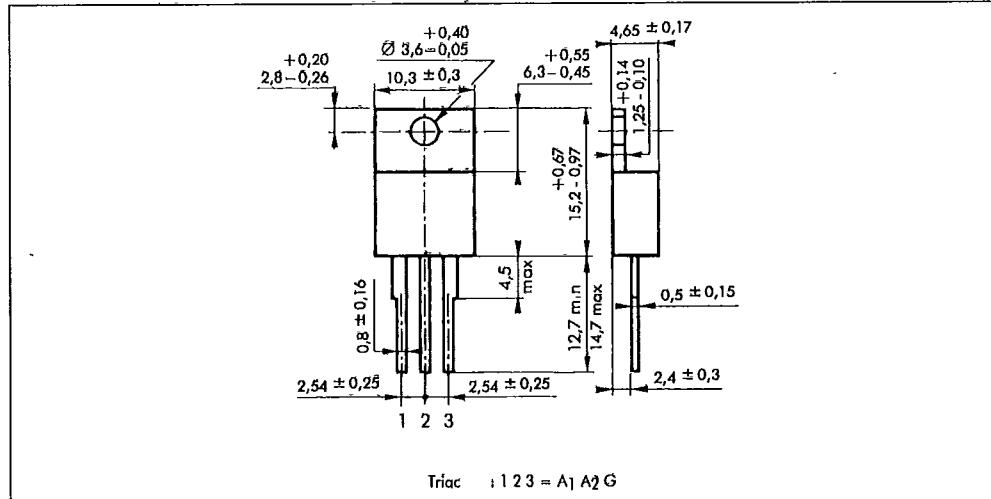
## ELECTRICAL CHARACTERISTICS

Symbol	Test Conditions			Quadrants	Min.	Typ.	Max.	Unit
$I_{GT}$	$T_J = 25^\circ\text{C}$	$V_D = 12 \text{ V}$	$R_L = 33 \Omega$	I-II-III-IV			10	mA
$V_{GT}$	$T_J = 25^\circ\text{C}$	$V_D = 12 \text{ V}$	$R_L = 33 \Omega$	I-II-III-IV			1.5	V
$V_{GD}$	$T_J = 110^\circ\text{C}$	$V_D = V_{DRM}$	$R_L = 3.3 \text{ k}\Omega$	I-II-III-IV	0.2			V
$I_H^*$	$T_J = 25^\circ\text{C}$	$I_T = 100 \text{ mA}$	Gate Open				25	mA
$I_L$	$T_J = 25^\circ\text{C}$	$V_D = 12 \text{ V}$	$I_G = 20 \text{ mA}$	I-III-IV		25		mA
$I_L$				II		50		mA
$V_{TM}^*$	$T_J = 25^\circ\text{C}$	$I_{TM} = 11 \text{ A}$	$t_p = 10 \mu\text{s}$				1.75	V
$I_{DRM}^*$	$V_{DRM}$ Specified		$T_J = 25^\circ\text{C}$				0.01	mA
			$T_J = 110^\circ\text{C}$				0.5	mA
$dv/dt^*$	$T_J = 110^\circ\text{C}$	Gate Open Linear Slope up to $V_D = 67\% V_{DRM}$			10			V/ $\mu\text{s}$
$(dv/dt)_c^*$	$T_C = 75^\circ\text{C}$	$V_D = V_{DRM}$	$I_T = 11 \text{ A}$			5		V/ $\mu\text{s}$
$t_{gt}$	$T_J = 25^\circ\text{C}$	$V_D = V_{DRM}$	$I_T = 11 \text{ A}$	I-II-III-IV		2		$\mu\text{s}$
	$I_G = 40 \text{ mA}$		$di/dt = 0.45 \text{ A}/\mu\text{s}$					

\* For either polarity of electrode A<sub>2</sub> voltage with reference to electrode A<sub>1</sub>.

## PACKAGE MECHANICAL DATA

TO 220 AB Plastic

Triac : 1 2 3 = A<sub>1</sub> A<sub>2</sub> G

Cooling method : by conduction (method C)

Marking : type number

Weight : 2 g

## T-25-15

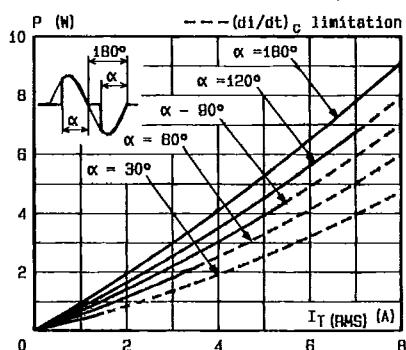


Fig.1 - Maximum mean power dissipation versus RMS on-state current ( $F = 60$  Hz).

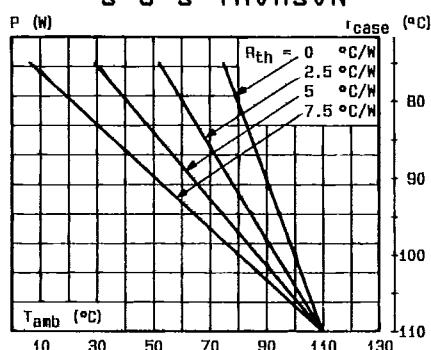


Fig.2 - Correlation between maximum mean power dissipation and maximum allowable temperatures ( $T_{amb}$  and  $T_{case}$ ) for different thermal resistances heatsink + contact.

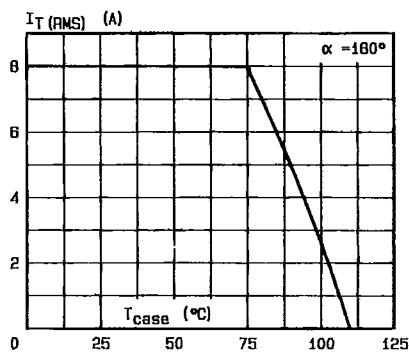


Fig.3 - RMS on-state current versus case temperature.

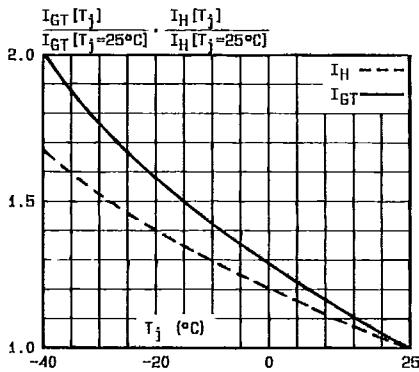


Fig.5 - Relative variation of gate trigger current and holding current versus junction temperature.

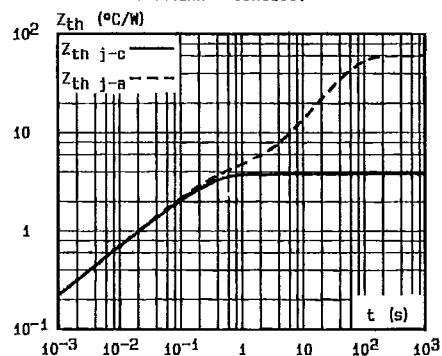


Fig.4 - Thermal transient impedance junction to case and junction to ambient versus pulse duration.

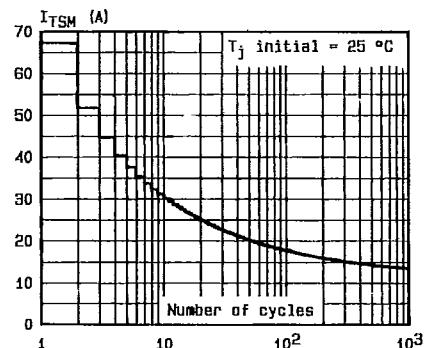


Fig.6 - Non repetitive surge peak on-state current versus number of cycles.

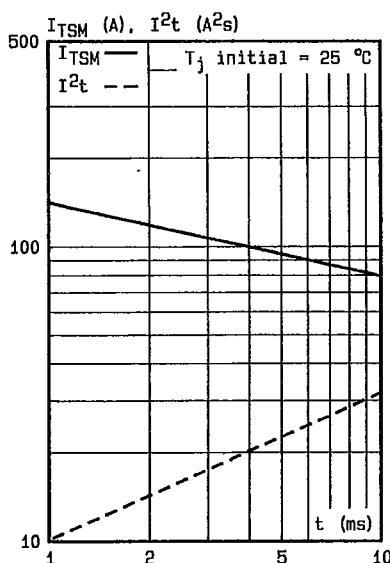


Fig.7 - Non repetitive surge peak on-state current for a sinusoidal pulse with width :  $t \leq 10$  ms, and corresponding value of  $I^2t$ .

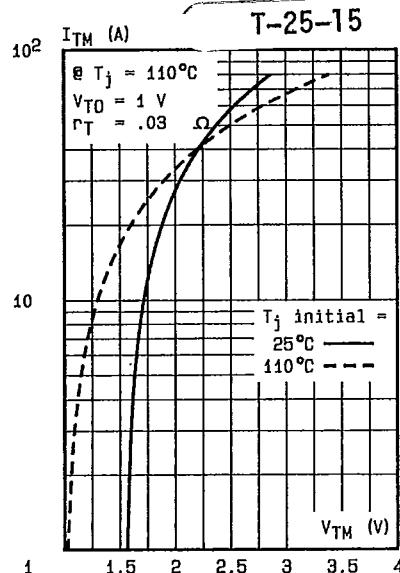


Fig.8 - On-state characteristics (maximum values).